

Description

The SX180P04T6 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -40V$ $I_D = -180A$

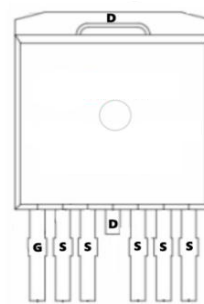
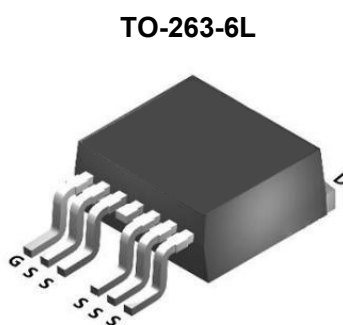
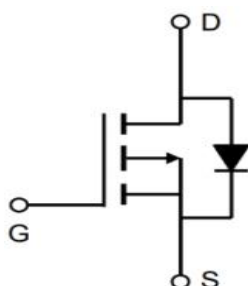
$R_{DS(ON)} < 2.8m\Omega$ @ $V_{GS} = -10V$

Application

Battery protection

Load switch

Uninterruptible power supply



Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-180	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-120	A
I_{DM}	Pulsed Drain Current ²	-540	A
EAS	Single Pulse Avalanche Energy ³	1020	mJ
I_{AS}	Avalanche Current	-80	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	350	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62.5	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	0.9	$^\circ C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-40	-44	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.023	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-20A	---	1.98	2.8	mΩ
		V _{GS} =-4.5V, I _D =-10A	---	2.9	3.5	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.6	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-40V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =-40V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-15V, I _D =-12A	---	125	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.2	---	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-20V, V _{GS} =-10V, I _D =-40	---	236	---	nC
Q _{gs}	Gate-Source Charge		---	26	---	
Q _{gd}	Gate-Drain Charge		---	44	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-20V, V _{GS} =-10V, R _G =3.0Ω, I _D =-40	---	32	---	ns
T _r	Rise Time		---	34	---	
T _{d(off)}	Turn-Off Delay Time		---	136	---	
T _f	Fall Time		---	40	---	
C _{iss}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1MHz	---	13276	---	pF
C _{oss}	Output Capacitance		---	1900	---	
C _{rss}	Reverse Transfer Capacitance		---	1470	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	-18	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、The EAS data shows Max. rating . The test condition is V_{DD}=-32V,V_{GS}=-10V,L=0.1mH,I_{AS}=-80
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

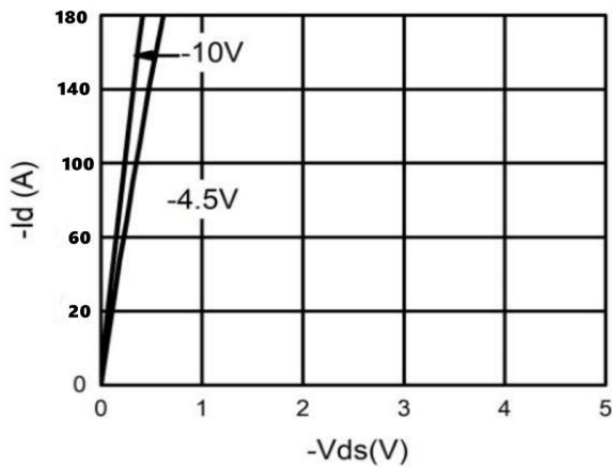


Fig 1. Output Characteristics

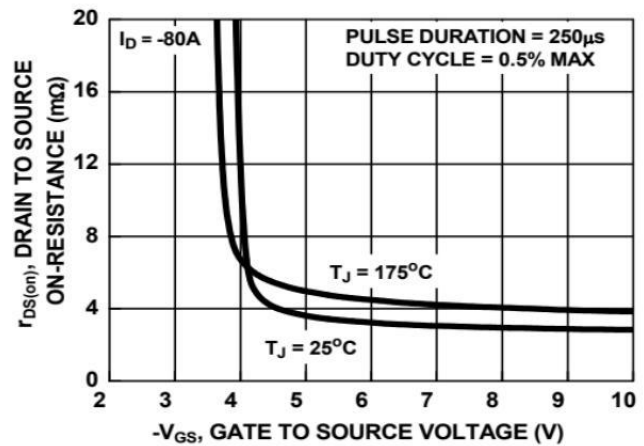


Fig 2. RDSON vs. Gate Voltage

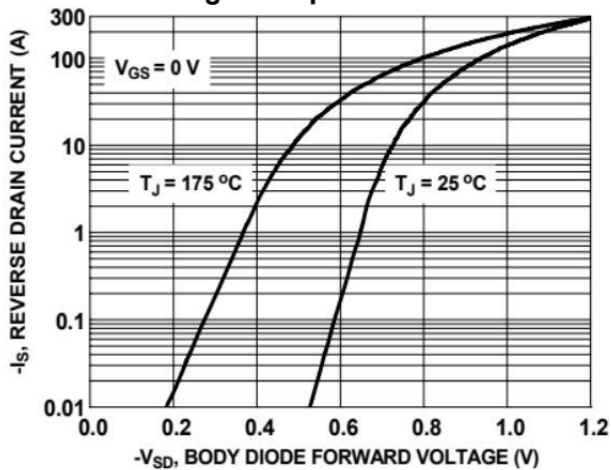


Fig3. Forward Diode Characteristics

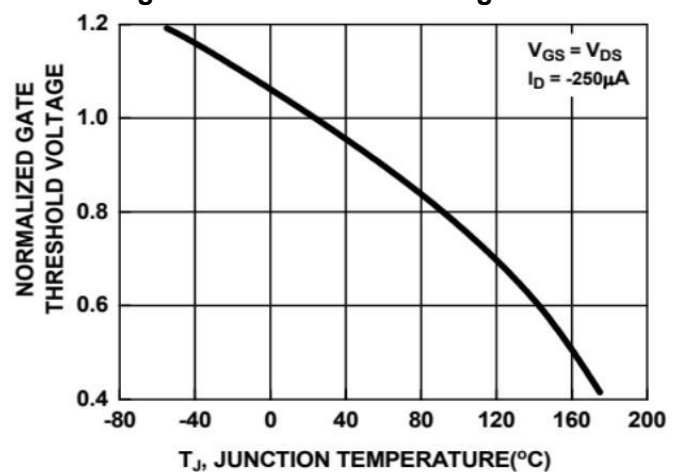


Fig4. Normalized Gate Threshold Voltage vs. Temperature

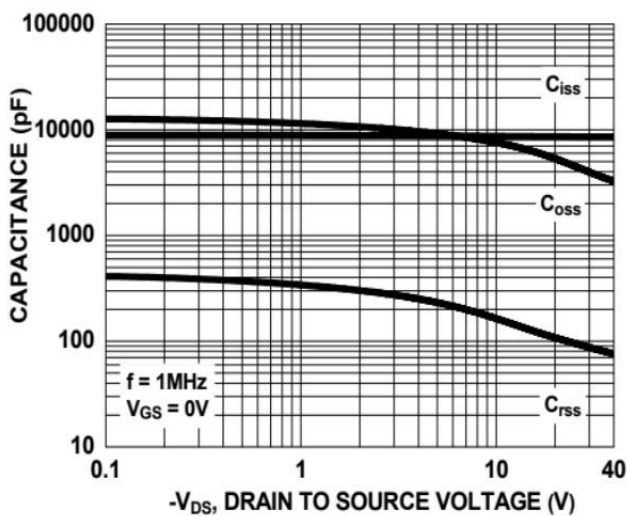


Fig5. Capacitance vs. Drain to Source Voltage

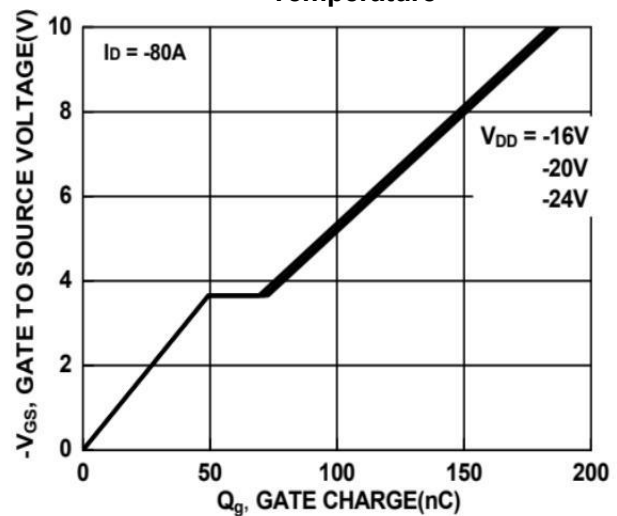
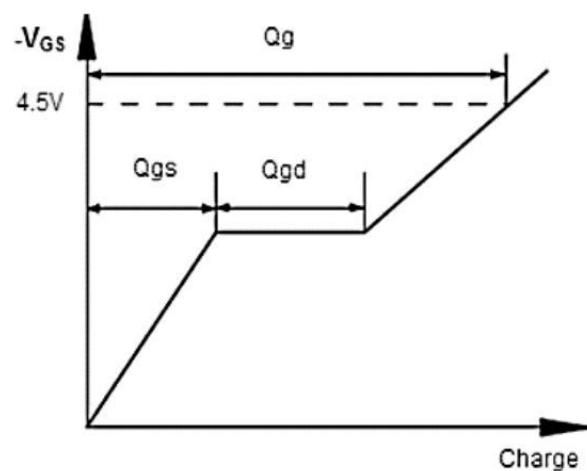
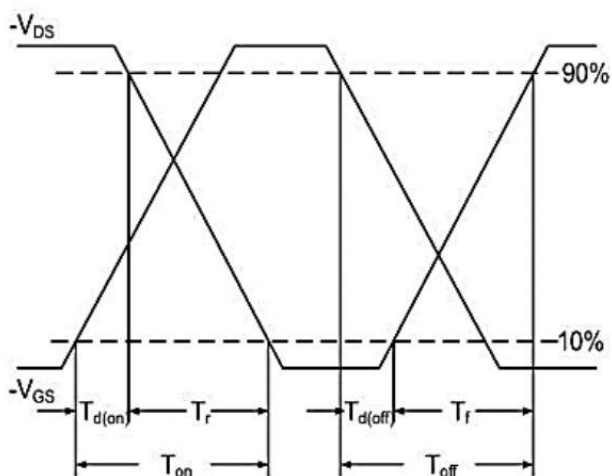
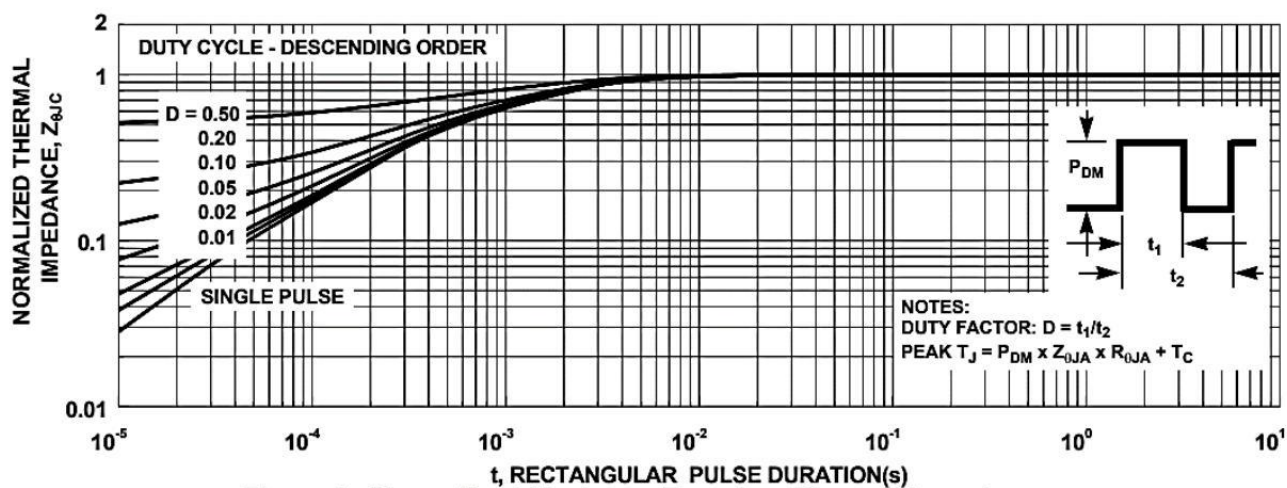
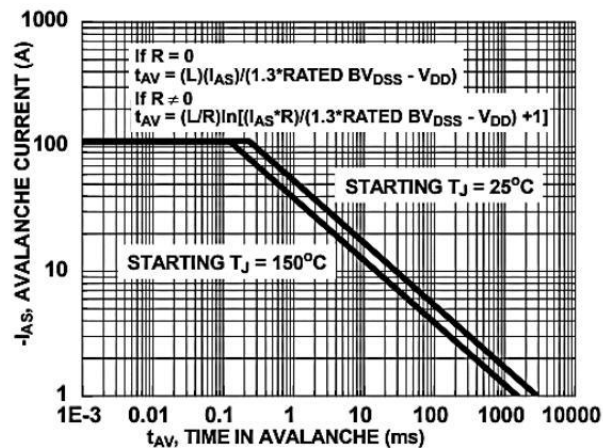
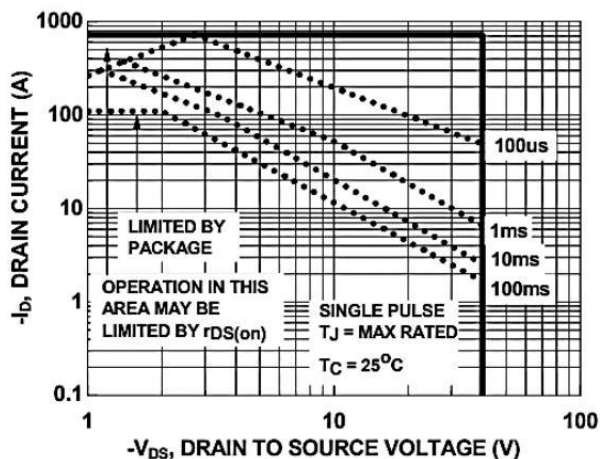
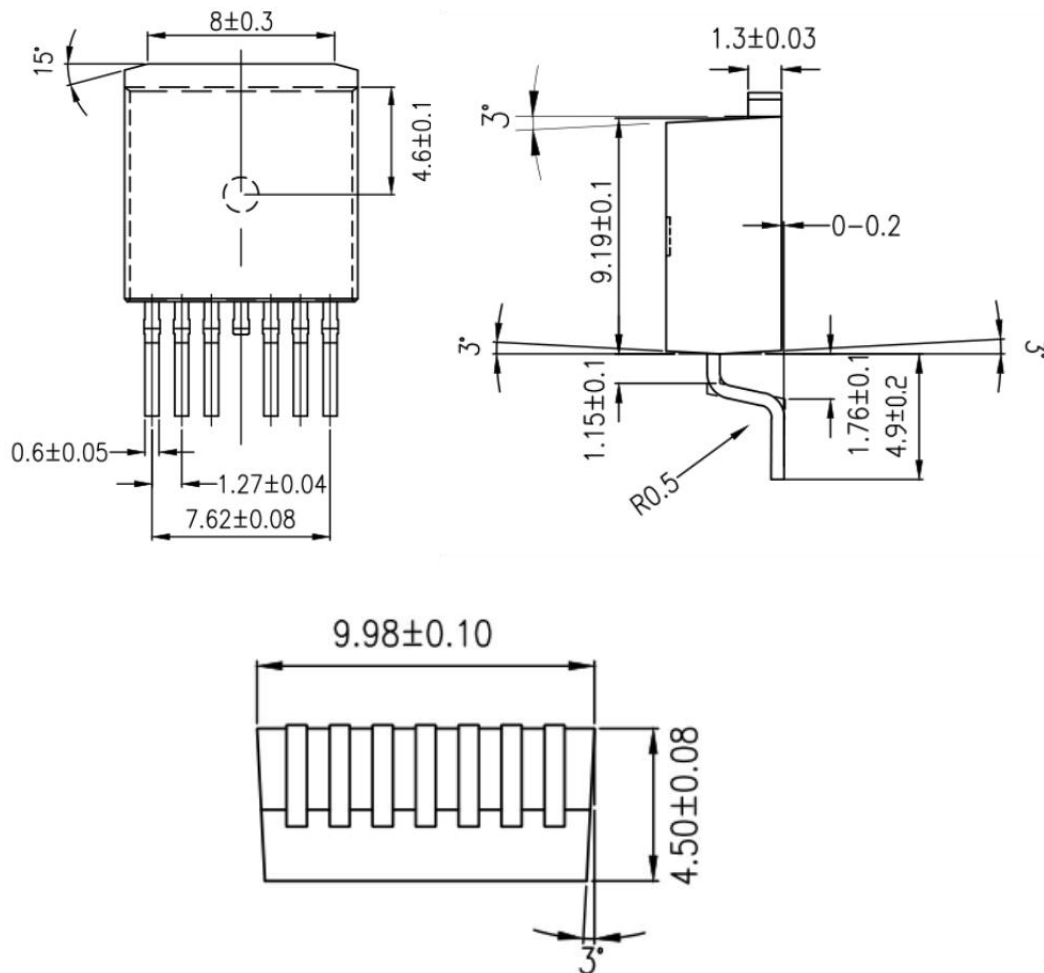


Fig6. Gate Charge vs. Gate to Source Voltage

Typical Characteristics



Package Mechanical Data:TO263-6L



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO263-6L		800